



Thyristor/Diode Modules

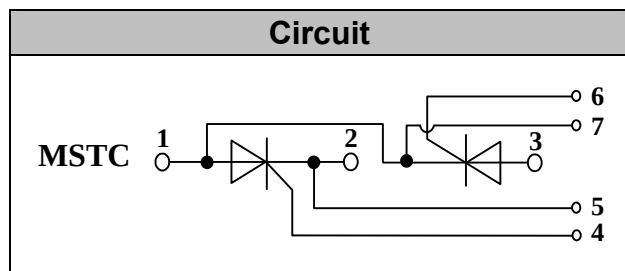
V_{RRM} / V_{DRM} 800 to 1600V
I_{TAV} 40Amp

Applications

- Power Converters
- Lighting Control
- DC Motor Control and Drives
- Heat and temperature control

Features

- International standard package
- High Surge Capability
- Glass passivated chip
- Simple Mounting
- Heat transfer through aluminum oxide DCB ceramic isolated metal baseplate



Module Type

TYPE	V _{RRM}	V _{RSM}
MSTC40-08	800V	900V
MSTC40-12	1200V	1300V
MSTC40-16	1600V	1700V

Maximum Ratings

Symbol	Conditions	Values	Units
I _{TAV}	Sine 180°; T _c =85°C	40	A
I _{TSM}	T _{VJ} =45°C t=10ms, sine T _{VJ} =125°C t=10ms, sine	1000 850	A
i ² t	T _{VJ} =45°C t=10ms, sine T _{VJ} =125°C t=10ms, sine	5000 3600	A ² s
Visol	a.c.50HZ;r.m.s.;1min	3000	V
T _{vj}		-40 to 125	°C
T _{stg}		-40 to 125	°C
M _t	To terminals(M5)	3 ± 15%	Nm
M _s	To heatsink(M6)	5 ± 15%	Nm
di/dt	T _{VJ} = T _{VJM} , 2/3V _{DRM} , I _G =500mA Tr<0.5us, tp>6us	150	A/us
dv/dt	T _J = T _{VJM} , 2/3V _{DRM} linear voltage rise	1000	V/us
a	Maximum allowable acceleration	50	m/s ²
Weight	Module(Approximately)	100	g

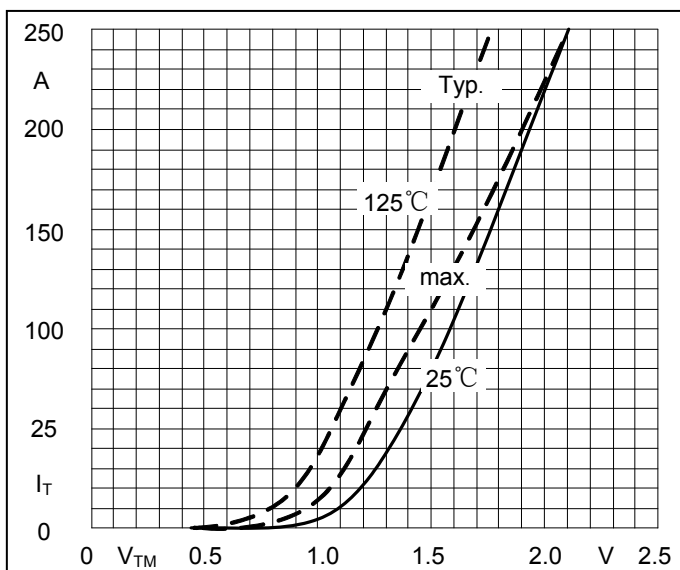
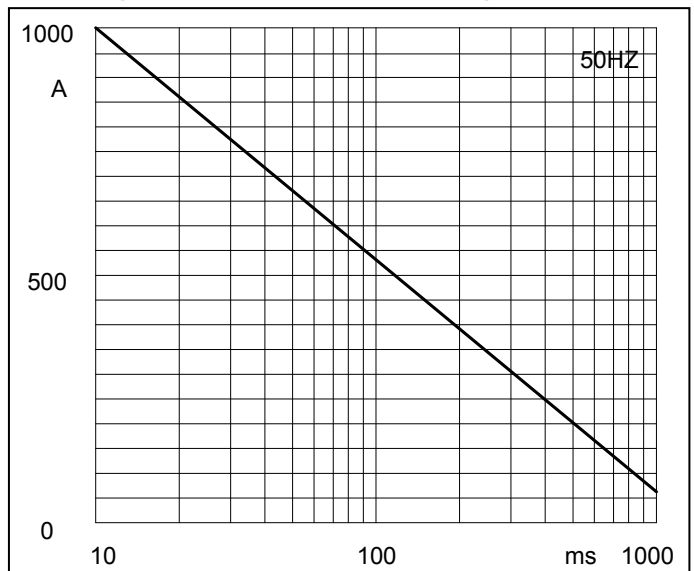
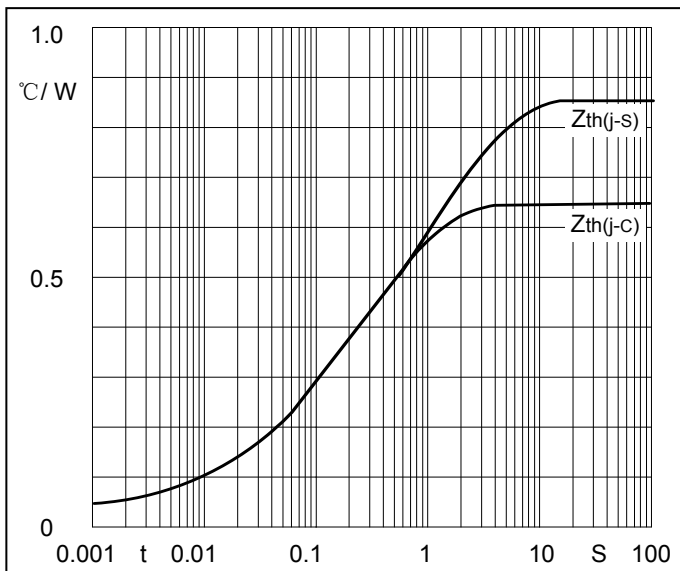
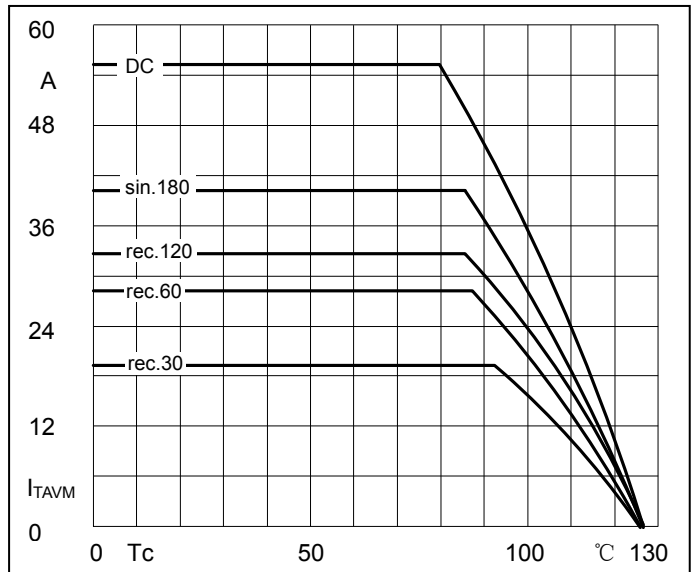
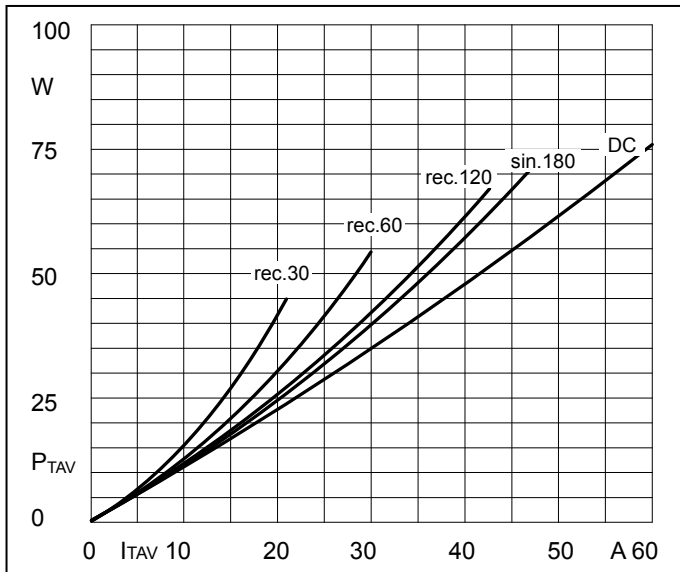
Thermal Characteristics

Symbol	Conditions	Values	Units
R _{th(j-c)}	Cont.;per thyristor / per module	0.65/0.33	°C/W
R _{th(c-s)}	per thyristor / per module	0.2/0.1	°C/W

Electrical Characteristics

Symbol	Conditions	Values			Units
		Min.	Typ.	Max.	
V_{TM}	$T=25^{\circ}\text{C}$ $I_{TM}=200\text{A}$			1.95	V
I_{RRM}/I_{DRM}	$T_{VJ}=T_{VJM}$, $V_R=V_{RRM}$, $V_D=V_{DRM}$			15	mA
V_{TO}	For power-loss calculations only ($T_{VJ}=125^{\circ}\text{C}$)			1.0	V
r_T	$T_{VJ}=T_{VJM}$			4.5	mΩ
V_{GT}	$T_{VJ}=25^{\circ}\text{C}$, $V_D=6\text{V}$			2.5	V
I_{GT}	$T_{VJ}=25^{\circ}\text{C}$, $V_D=6\text{V}$			150	mA
V_{GD}	$T_{VJ}=125^{\circ}\text{C}$, $V_D=2/3V_{DRM}$			0.25	V
I_{GD}	$T_{VJ}=125^{\circ}\text{C}$, $V_D=2/3V_{DRM}$			6	mA
I_L	$T_{VJ}=25^{\circ}\text{C}$, $R_G=33\ \Omega$		300	600	mA
I_H	$T_{VJ}=25^{\circ}\text{C}$, $V_D=6\text{V}$		150	250	mA
tgδ	$T_{VJ}=25^{\circ}\text{C}$, $I_G=1\text{A}$, $di_G/dt=1\text{A}/\mu\text{s}$	1			μs
tq	$T_{VJ}=T_{VJM}$	80			μs

Performance Curves



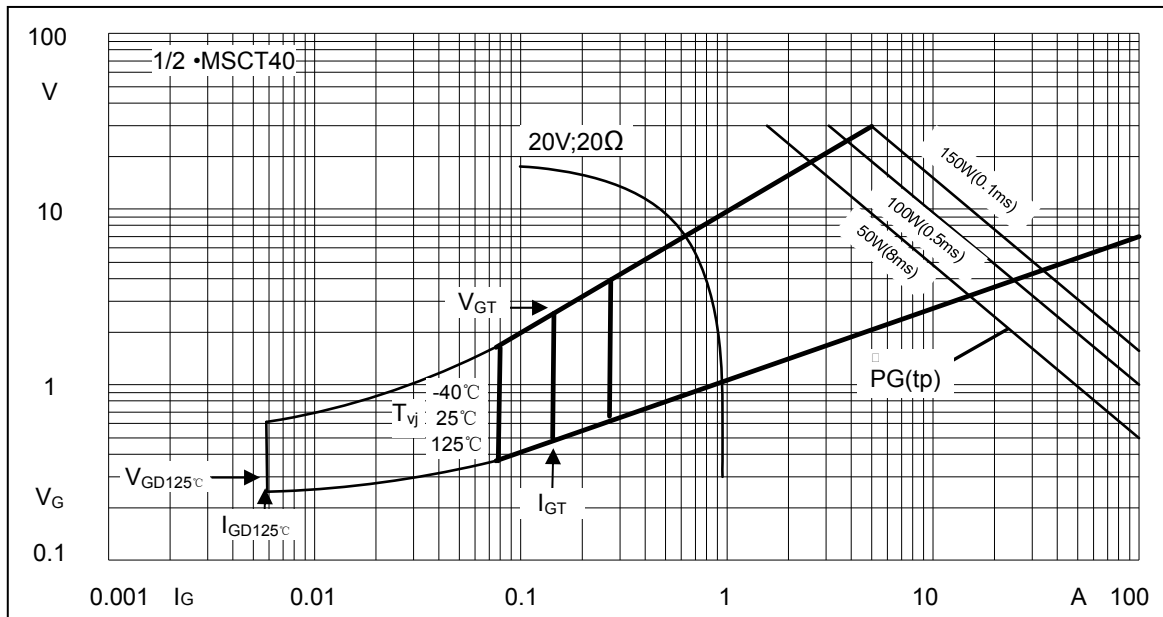
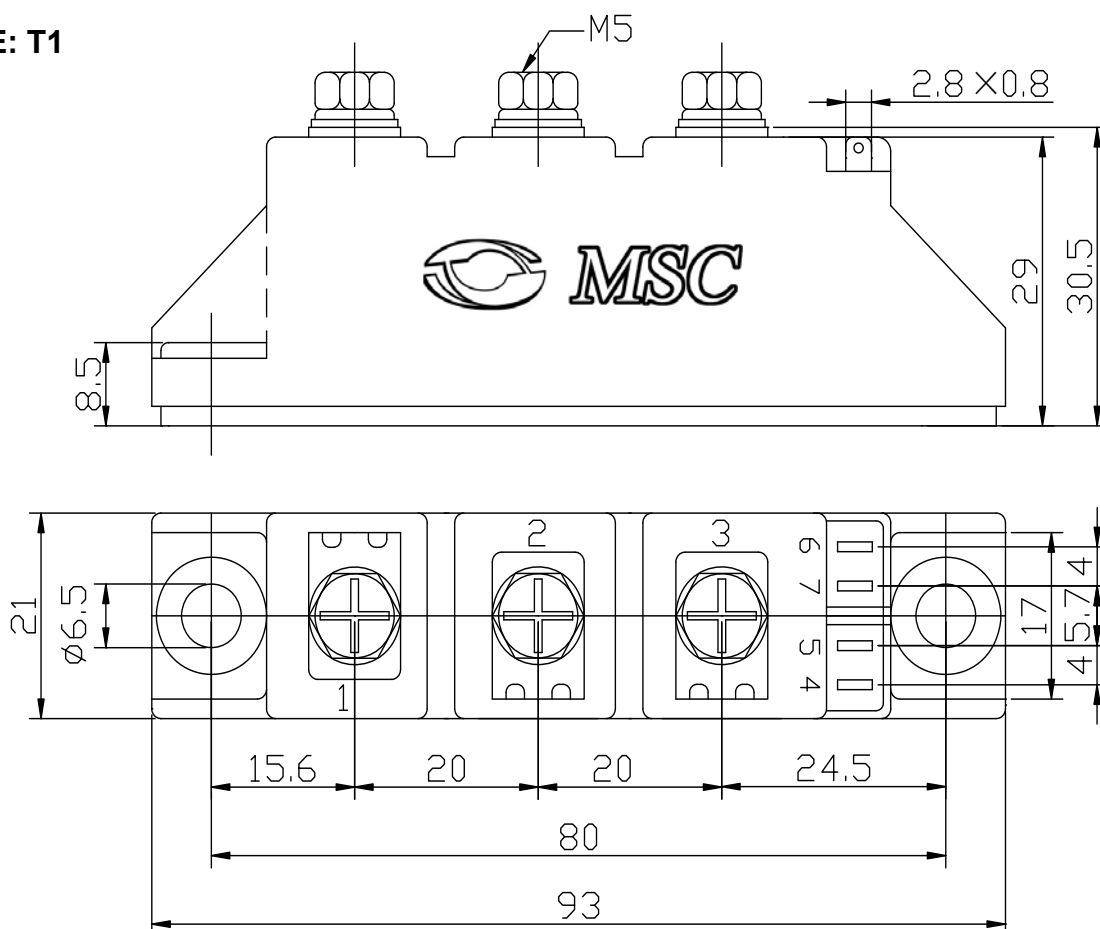


Fig6. Gate trigger Characteristics

Package Outline Information

CASE: T1



Dimensions in mm